

Inverting Dual (-V_{IN}, -2V_{IN}) Charge Pump Voltage Converters with Shutdown

FEATURES

- 10-Pin MSOP Package
- Operates from 1.8V to 5.5V
- Up to 5mA Output Current at -V_{IN} Pin
- Up to 1mA Output Current at -2V_{IN} Pin
- Power-Saving Shutdown Mode
- -V_{IN} and -2V_{IN} Outputs Available
- Low Active Supply Current

■ Fully Compatible with 1.8V Logic Systems

TYPICAL APPLICATIONS

- LCD Panel Bias
- Cellular Phones PA Bias
- Pagers
- PDAs, Portable Dataloggers
- **■** Battery Powered Devices

input voltage can range from +1.8V to +5.5V.

ORDERING INFORMATION

supply current.

GENERAL DESCRIPTION

Part No.	Package (Osc Freq	(KHz) Temp Ran	ge
TC1235EUN	10-Pin MSC)P 12	–40°C to +8	5°C
TC1236EUN	10-Pin MSC	DP 35	–40°C to +8	5°C
TC1237EUN	10-Pin MSC)P 125	-40°C to +8	5°C

The TC1235/1236/1237 are CMOS dual inverting

charge pump voltage converters with a low power shutdown

mode in MSOP 10-Pin packages. Only four external capaci-

tors are required for full circuit implementation. Switching

frequencies are 12kHz for the TC1235, 35kHz for the

TC1236 and 125kHz for the TC1237. When the shutdown

pin is held at a logic low, the device goes into a very low

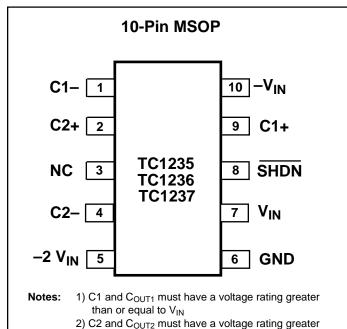
power mode of operation, consuming less than 1µA of

sion (available at the $-V_{IN}$ output), and a negative doubling voltage inversion (available at the -2 V_{IN} output) with a low output impedance capable of providing output currents up to

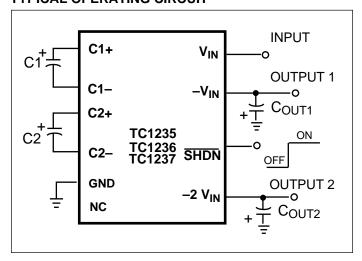
5mA for the $-V_{IN}$ output and 1mA for the $-2V_{IN}$ output. The

These devices provide both a negative voltage inver-

PIN CONFIGURATION



TYPICAL OPERATING CIRCUIT



than or equal to 2V_{IN}

TC1235 TC1236 TC1237

ABSOLUTE MAXIMUM RATINGS*

Input Voltage (V _{IN} to GND)	. +6.0V, -0.3V
Output Voltage (-V _{IN} , -2V _{IN} to GND)	
Current at $-V_{IN}$, $-2V_{IN}$ Pins	10mA
Short-Circuit Duration -V _{IN} , -2V _{IN} to GND	Indefinite
Operating Temperature Range	- 40°C to +85°C

Power Dissipation ($T_A \le 70^{\circ}C$) MSOP-10320mW Storage Temperature (Unbiased) - 65°C to +150°C Lead Temperature (Soldering, 10sec)+260°C

*This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS: $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{\text{IN}} = +5\text{V}$, $C1 = 3.3 \mu\text{F}$, $C2 = 1 \mu\text{F}$ (TC1235); $C1 = 1 \mu\text{F}$, $C2 = 1 \mu\text{F}$ = $0.33\mu F$ (TC1236); C1 = $0.33\mu F$, C2 = $0.1\mu F$ (TC1237), $\overline{SHDN} = V_{IN}$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.

Symbol	Parameter	Device	Test Conditions	Min	Тур	Max	Unit
I _{DD}	Supply Current	TC1235 TC1236	SHDN = V _{IN} SHDN = V _{IN}	_	75 200	120 360	μΑ
		TC1237	SHDN = VIN	_	625	1500	
I _{SHDN}	Shutdown Supply Current	All	SHDN = GND, V _{IN} = +5V	_	0.1	1	μΑ
V _{MIN}	Minimum Supply Voltage	All	$R_{LOAD} = 1k\Omega$ for $-V_{IN}$ output $R_{LOAD} = 10k\Omega$ for $-2V_{IN}$ output	1.8	_	_	V
V_{MAX}	Maximum Supply Voltage	All	$R_{LOAD} = 1k\Omega$ for $-V_{IN}$ output $R_{LOAD} = 10k\Omega$ for $-2V_{IN}$ output	_	_	5.5	V
Fosc	Oscillator Frequency	TC1235 TC1236 TC1237		8.4 24.5 65	12 35 125	15.6 45.5 170	kHz
V _{IH}	Shutdown Input Logic High	All	$V_{IN} = V_{MIN}$ to V_{MAX}	1.4	_	_	V
V _{IL}	Shutdown Input Logic low	All	$V_{IN} = V_{MIN}$ to V_{MAX}	_	_	0.4	V
V _{EFF1}	Voltage Conversion Efficiency (Stage 1)	All	$R_{LOAD} = \infty$ for $-V_{IN}$ output $R_{LOAD} = \infty$ for $-2V_{IN}$ output	96	99.5	_	%
V _{EFF2}	Voltage Conversion Efficiency (Stage 2)	All	$R_{LOAD} = \infty$ for $-V_{IN}$ output $R_{LOAD} = \infty$ for $-2V_{IN}$ output	94	99	_	%
R _{OUT1}	Output Resistance for –V _{IN} output (Note 1)	All	I _{LOAD} = 0.5mA to 5mA No Load at -V _{IN} Output	_	45	80	Ω
R _{OUT2}	Output Resistance for –2V _{IN} output (Note 1)	All	I _{LOAD} = 0.1mA to 1mA No Load at -2V _{IN} Output	_	135	420	Ω
T _{WK1}	Wake-Up Time	TC1235	$R_{LOAD} = 1k\Omega$ for $-V_{IN}$ Output	_	650	_	μsec
	From Shutdown Mode Stage 1	TC1236 TC1237	$R_{LOAD} = 10k\Omega$ for $-2V_{IN}$ Output		250 100	_	
T _{WK2}	Wake-Up Time From Shutdown Mode Stage 2	TC1235 TC1236 TC1237	R_{LOAD} = 1kΩ for -V _{IN} Output R_{LOAD} = 10kΩ for -2V _{IN} Output		750 280 120	_	μsec

NOTES: 1. Capacitor contribution is approximately 20% of the output impedance [ESR = 1 / pump frequency x capacitance)].

PIN DESCRIPTION

Pin Number Name		Description
1	C1-	C1 Commutation Capacitor Negative Terminal.
2	C2+	C2 Commutation Capacitor Positive Terminal.
3	NC	No Connection.
4	C2— C2 Commutation Capacitor Negative Terminal.	
5	-2V _{IN}	Doubling Inverting Charge Pump Output (–2 x V _{IN}).
6 GND Ground.		Ground.
7	V_{IN}	Positive Power Supply Input.
8 SHDN Shutdown Input (Active Low).		Shutdown Input (Active Low).
9	C1+	C1 Commutation Capacitor Positive Terminal.
10 –V _{IN} Inverting Charge Pump Output (–1 x V _{IN}).		Inverting Charge Pump Output (–1 x V _{IN}).

DETAILED DESCRIPTION

The TC1235/1236/1237 dual charge pump converters perform both a -1x and -2x multiply of the voltage applied to the V_{IN} pin. Output '- V_{IN} ' provides a negative voltage inversion of the V_{IN} supply, while output '-2 V_{IN} ' provides a negative doubling inversion of V_{IN} . Conversion is performed using two **synchronous** switching matrices and four external capacitors. When the shutdown input is held at a logic low both stages go into a very low power mode of operation consuming less than 1uA of supply current.

Figure 1 (below) is a block diagram representation of the TC1235/1236/1237 architecture. The first switching stage inverts the voltage present at V_{IN} and the second stage uses the ' $-V_{IN}$ ' output generated from the first stage to produce the ' $-2V_{IN}$ ' output function from the second stage switching matrix.

Each device contains an on-board oscillator that synchronously controls the operation of the charge pump switching matrices. The TC1235 synchronously switches at 12KHz, the TC1236 synchronously switches at 35KHz, and the TC1237 synchronously switches at 125KHz. The different oscillator frequencies for this device family allow the user to trade-off capacitor size versus supply current. Faster oscillators can use smaller external capacitors but will consume more supply current (see Electrical Characteristics Table).

When the shutdown input is in a low state, the oscillator and both switch matrices are powered off placing the TC1235/1236/1237 in the shutdown mode. When the V_{IN} supply input is powered from an external battery, the shutdown mode minimizes power consumption, which in turn will extend the life of the battery.

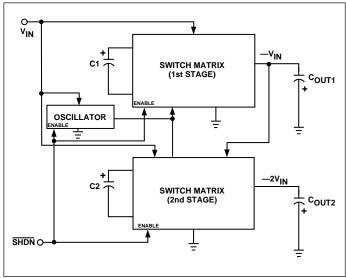


Figure 1. Functional Block Diagram

APPLICATIONS INFORMATION

Output Voltage Considerations

The TC1235/1236/1237 performs voltage conversions but does not provide any type of regulation. The two output voltage stages will droop in a linear manner with respect to their respective load currents. The value of the equivalent output resistance of the '-V_{IN}' output is approximately 50Ω nominal at +25°C and V_{IN} = +5V. The value of the '-2V_{IN}' output and is approximately 140 Ω nominal at +25°C and V_{IN} = +5V. In this particular case, '-V_{IN}' is approximately -5V and '-2V_{IN}' is approximately -10V at very light loads, and each stage will droop according to the equation below:

$$\begin{split} V_{DROOP} &= I_{OUT} \times R_{OUT} \\ &[-V_{IN} \ OUTPUT] = V_{OUT1} = - (V_{IN} - V_{DROOP1}) \\ &[-2V_{IN} \ OUTPUT] = V_{OUT2} = V_{OUT1} - (V_{IN} - V_{DROOP2}) \end{split}$$

where V_{DROOP1} is the output voltage droop contributed from stage 1 loading , and V_{DROOP2} is the output voltage droop from stage 2 loading.

Charge Pump Efficiency

The overall power efficiency of the two charge pump stages is affected by four factors:

- (1) Losses from power consumed by the internal oscillator, switch drive, etc. (which vary with input voltage, temperature and oscillator frequency).
- (2) I²R losses due to the on-resistance of the MOSFET switches on-board each charge pump.
- (3) Charge pump capacitor losses due to effective series resistance (ESR).
- (4) Losses that occur during charge transfer (from the commutation capacitor to the output capacitor) when a voltage difference between the two capacitors exists.

Most of the conversion losses are due to factor (2), (3) and (4) above. The losses for the first stage are given by Equation 1a and the losses for the second stage are given by Equation 1b.

$$P1_{LOSS (2, 3, 4)} = I_{OUT1}^{2} x R_{OUT1}$$

where $R_{OUT1} = [1 / [f_{OSC}(C1)] + 8R_{SWITCH1} + 4ESR_{C1} + ESR_{COUT1}]$

Inverting Dual (-V_{IN}, -2V_{IN}) Charge Pump Voltage Converters with Shutdown

 $P2_{LOSS (2, 3, 4)} = I_{OUT2}^{2} x R_{OUT2}$ where $R_{OUT2} = [1 / [f_{OSC}(C2)] + 8R_{SWITCH2} + 4ESR_{C2} + ESR_{COUT2}]$

Equation 1b.

The internal switch resistance for the first stage (i.e. $R_{SWITCH1}$) is approximately 3Ω and the switch resistance for the second stage (i.e. $R_{SWITCH2}$) is approximately 7Ω .

The losses in the circuit due to factor (4) above are also shown in Equation 2a for stage 1 and Equation 2b for stage 2. The output voltage ripple for stage 1 is given by Equation 3a and the output voltage ripple for stage 2 is given by Equation 3b.

$$P_{LOSS1 (4)} = [(0.5)(C1)(V_{IN}^2 - V_{OUT1}^2) + (0.5) (C_{OUT1}) (V_{RIPPLE1}^2 - 2V_{OUT1} V_{RIPPLE1})] x fosc$$

Equation 2a.

$$P_{LOSS2 (4)} = [(0.5) (C2) (V_{IN}^2 - V_{OUT2}^2) + (0.5) (C_{OUT2}) (V_{RIPPLE2}^2 - 2V_{OUT2} V_{RIPPLE2})] x fosc$$

Equation 2b.

$$V_{RIPPLE1} = [I_{OUT1} / (f_{OSC}) (C_{OUT1})] + 2 (I_{OUT1})$$
(ESR_{COUT1})

Equation 3a.

$$V_{RIPPLE2} = [I_{OUT2} / (f_{OSC}) (C_{OUT2})] + 2 (I_{OUT2})$$
(ESR_{COUT2})

Equation 3b.

Capacitor Selection

In order to maintain the lowest output resistance and output ripple voltage, it is recommended that low ESR capacitors be used. Additionally, larger values of C1 and C2 will lower the output resistance and larger values of C_{OUT1} and C_{OUT2} will reduce output ripple. (See Equations 1a, 1b, 3a, and 3b). NOTE: For proper charge pump operation, C1 and C_{OUT1} must have a voltage rating greater than or equal to V_{IN} , while C2 and C_{OUT2} must have a voltage rating greater than or equal to $2V_{IN}$.

Table 1a shows various values of C1 and the corresponding output resistance values for $V_{IN}=5V$ @ $+25^{\circ}C$ for stage 1 and Table 1b shows various values of C2 and the corresponding output resistance values for $V_{IN}=5V$ @ $+25^{\circ}C$ for stage 2. It assumes a 0.1Ω ESR_{C1}, a 0.1Ω ESR_{C2}, a 3Ω R_{SWITCH1}, and a 7Ω R_{SWITCH2}.

Table 2a shows the output voltage ripple for various values of C_{OUT1} and Table 2b shows the output voltage ripple for various values of C_{OUT2} (again assuming $V_{IN} = 5V$ @ +25°C). The $V_{RIPPLE1}$ values assume a 3mA output load current for stage 1 and a 0.1 Ω ESR_{COUT1}. The $V_{RIPPLE2}$ values assume a 200 μ A output load current for stage 2 and a 0.1 Ω ESR_{COUT1}.

Table 1a. Output Resistance vs. C1 (ESR = 0.1Ω). For Stage 1

C1 (µF)	TC1235 R _{OUT} (Ω)	TC1236 R _{OUT} (Ω)	TC1237 R _{OUT} (Ω)
0.47	202	85	42
1	108	53	33
3.3	50	33	27

Table 1b. Output Resistance vs. C2 (ESR = 0.1Ω). For Stage 2

C2 (µF)	TC1235 R _{OUT} (Ω)	TC1236 R _{OUT} (Ω)	TC1237 R _{OUT} (Ω)
0.1	890	342	137
0.47	239	117	74
1	140	85	65

Table 2a. Output Voltage Ripple vs. C_{OUT1} (ESR = 0.1 Ω) For Stage 1 (I_{OUT1} = 3mA)

C _{OUT1} (µF)	TC1235 V _{RIPPLE1} (mV)	TC1236 V _{RIPPLE1} (mV)	TC1237 V _{RIPPLE1} (mV)
0.47	533	183	52
1	251	86	25
3.3	76	27	8

Table 2b. Output Voltage Ripple vs. C_{OUT2} (ESR = 0.1 Ω) For Stage 2 (I_{OUT2} = 200 μ A)

	C _{OUT2} (µF)	TC1235 V _{RIPPLE2} (mV)	TC1236 V _{RIPPLE2} (mV)	TC1237 V _{RIPPLE2} (mV)	
	0.1	167	57	16	
	0.47	36	12	3.4	
	1	17	5.8	1.6	

Input Supply Bypassing

The $V_{\rm IN}$ input should be capacitively bypassed to reduce AC impedance and minimize noise effects due to the switching internal to the device. It is recommended that a large value capacitor (at least equal to C1) be connected from $V_{\rm IN}$ to GND for optimal circuit performance.

Shutdown Input

The TC12351/1236/1237 is enabled when /SHDN is high, and disabled when /SHDN is low. This input cannot be allowed to float. (If /SHDN is not required, see the TC1225/1226/1227 data sheet.) The /SHDN input should be limited to 0.3V above V_{IN} to avoid significant current flows.

Dual Voltage Inverter

The most common application for the TC1235/1236/1237 devices is the dual voltage inverter (Figure 2). This application uses four external capacitors: C1, C2, C_{OUT1} , and C_{OUT2} (NOTE: a power supply bypass capacitor is recommended). The outputs are equal to $-V_{IN}$ and -2VIN plus any voltage drops due to loading. Refer to Tables 1a, 1b, 2a, and 2b for capacitor selection guidelines.

Device	C _{IN}	C1	C2	C _{OUT1}	C _{OUT2}
TC1235	3.3µF	3.3µF	1μF	3.3µF	1μF
TC1236	1μF	1μF	0.33μF	1μF	0.33μF
TC1237	0.33μF	0.33μF	0.1μF	0.33μF	0.1μF

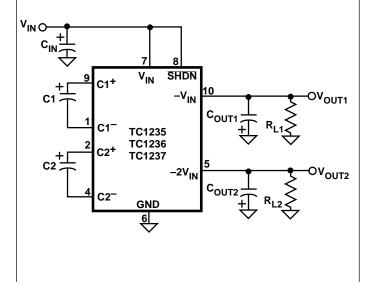


Figure 2. Dual Voltage Inverter Test Circuit

Layout Considerations

As with any switching power supply circuit good layout practice is recommended. Mount components as close together as possible to minimize stray inductance and capacitance. Also use a large ground plane to minimize noise leakage into other circuitry.

TC1235 DEMO Card

The TC1235 DEMO Card is a 2.0" x 2.0" card containing both a TC1235 and two cascaded TC1219s that allow the user to compare the operation of each approach for generating a –1X and –2X function. Each circuit is fully assembled with the required external capacitors along with variable load resistors that allow the user to vary the output load current of each stage. For convenience, several test points and jumpers are available for measuring various voltages and currents on the demo board.

Figure 3 is a schematic of the TC1235 DEMO Card, and Figure 4 shows the assembly drawing and artwork for the board. Table 3 lists the voltages that are monitored by the test points and Table 4 lists the currents that can be measured using the jumpers.

Table 3. TC1235 DEMO Card Test Points

TEST POINT	VOLTAGE MEASUREMENT
TP1 VIN [+5V]	
TP2	GROUND
TP3	GROUND
TP4	TC1219 U1 OUTPUT [-5V(1)]
TP5	TC1219 U2 OUTPUT [-10V(1)]
TP6	TC1235 STAGE 1 OUTPUT [-5V(2)]
TP7	TC1235 STAGE 2 OUTPUT [-10V(2)]
TP8	EXTERNAL /SHDN INPUT
TP9	TC1219 U1 /SHDN INPUT
TP10	TC1235 U3 /SHDN INPUT

Table 4. TC1235 DEMO Card Jumpers

JUMPER	CURRENT MEASUREMNT
J1	DUAL TC1219 QUIESCENT CURRENT
J2	TC1235 QUIESCENT CURRENT
J3	TC1219 U1 [-5V(1)] LOAD CURRENT
J4	TC1219 U2 [-10V(1)] LOAD CURRENT
J5	TC1235 STAGE 1 [-5V(2)] LOAD CURRENT
J6	TC1235 STAGE 2 [-10V(2)] LOAD CURRENT
J7	TC1219 U1 /SHDN INPUT CURRENT
J8	TC1235 U3 /SHDN INPUT CURRENT
J9	GROUND EXTERNAL /SHDN INPUT

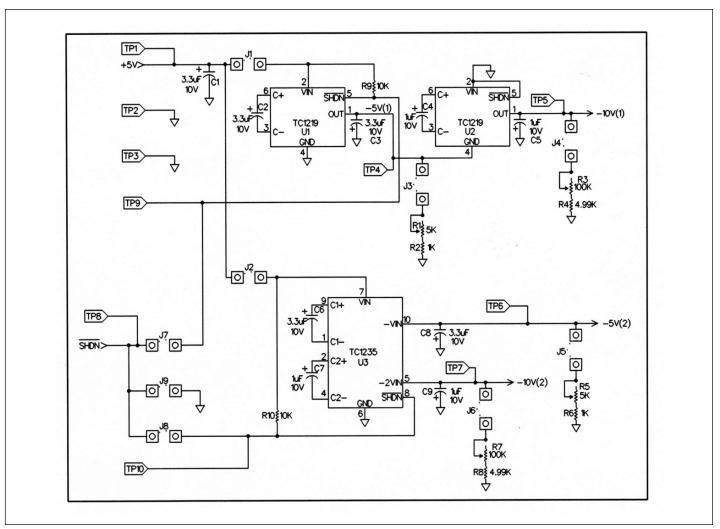


Figure 3. TC1235 DEMO Card Schematic

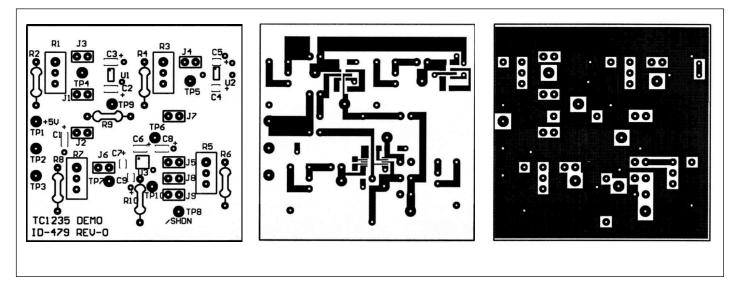
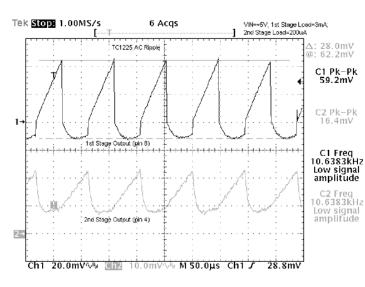
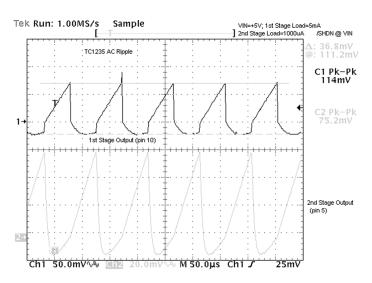
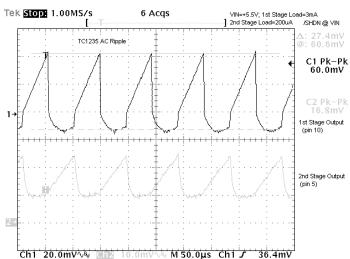


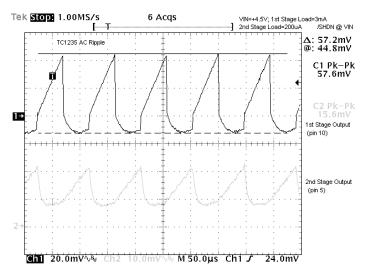
Figure 4. TC1235 DEMO Card Assembly Drawing and Artwork

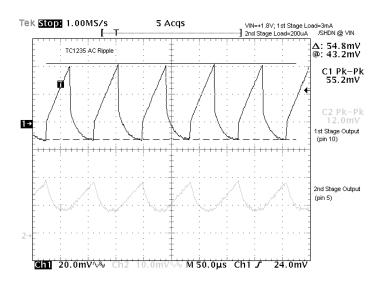
TYPICAL RIPPLE WAVEFORMS



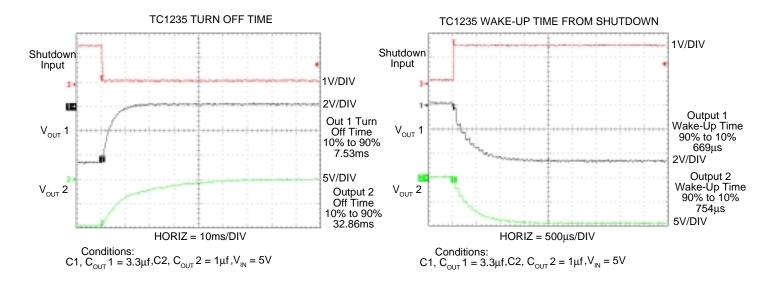




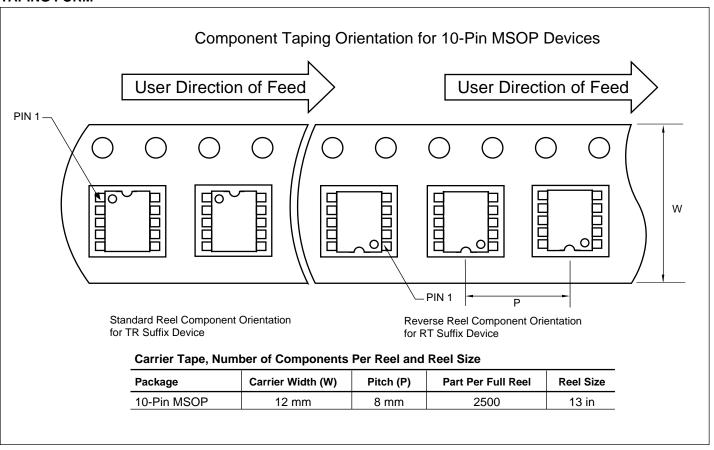




TYPICAL RIPPLE WAVEFORMS

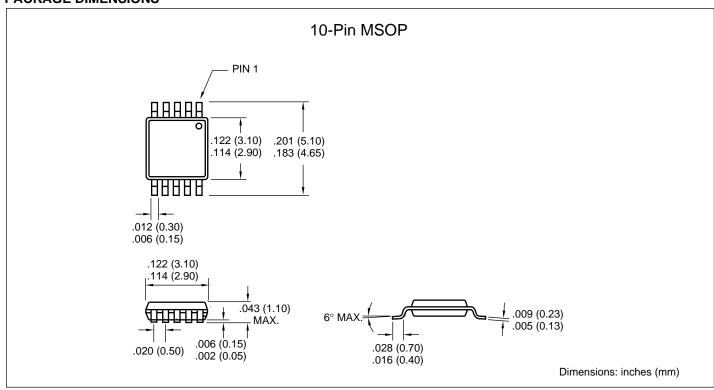


TAPING FORM



TC1235 TC1236 TC1237

PACKAGE DIMENSIONS





WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: 480-792-7627 Web Address: http://www.microchip.com

Rocky Mountain

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7966 Fax: 480-792-7456

Atlanta

500 Sugar Mill Road, Suite 200B Atlanta, GA 30350 Tel: 770-640-0034 Fax: 770-640-0307

Austin

Analog Product Sales 8303 MoPac Expressway North Suite A-201 Austin, TX 78759 Tel: 512-345-2030 Fax: 512-345-6085

Boston

2 Lan Drive, Suite 120 Westford, MA 01886 Tel: 978-692-3848 Fax: 978-692-3821

Boston

Analog Product Sales Unit A-8-1 Millbrook Tarry Condominium 97 Lowell Road Concord, MA 01742 Tel: 978-371-6400 Fax: 978-371-0050

Chicago

333 Pierce Road, Suite 180 Itasca, IL 60143 Tel: 630-285-0071 Fax: 630-285-0075

Dallas

4570 Westgrove Drive, Suite 160 Addison, TX 75001 Tel: 972-818-7423 Fax: 972-818-2924

Dayton

Two Prestige Place, Suite 130 Miamisburg, OH 45342 Tel: 937-291-1654 Fax: 937-291-9175

Detroit

Tri-Atria Office Building 32255 Northwestern Highway, Suite 190 Farmington Hills, MI 48334 Tel: 248-538-2250 Fax: 248-538-2260

Los Angeles

18201 Von Karman, Suite 1090 Irvine, CA 92612 Tel: 949-263-1888 Fax: 949-263-1338

Mountain View

Analog Product Sales 1300 Terra Bella Avenue Mountain View, CA 94043-1836 Tel: 650-968-9241 Fax: 650-967-1590 **New York**

150 Motor Parkway, Suite 202 Hauppauge, NY 11788 Tel: 631-273-5305 Fax: 631-273-5335

San Jose

Microchip Technology Inc. 2107 North First Street, Suite 590 San Jose, CA 95131 Tel: 408-436-7950 Fax: 408-436-7955

Toronto

6285 Northam Drive, Suite 108 Mississauga, Ontario L4V 1X5, Canada Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

China - Beijing

Microchip Technology Beijing Office New China Hong Kong Manhattan Bldg. No. 6 Chaoyangmen Beidajie Beijing, 100027, No. China Tel: 86-10-85282100 Fax: 86-10-85282104

China - Shanghai

Microchip Technology Shanghai Office Room 701, Bldg. B Far East International Plaza No. 317 Xian Xia Road Shanghai, 200051 Tel: 86-21-6275-5700 Fax: 86-21-6275-5060

Hong Kong

Microchip Asia Pacific RM 2101, Tower 2, Metroplaza 223 Hing Fong Road Kwai Fong, N.T., Hong Kong Tel: 852-2401-1200 Fax: 852-2401-3431

India

Microchip Technology Inc. India Liaison Office Divyasree Chambers 1 Floor, Wing A (A3/A4) No. 11, OíShaugnessey Road Bangalore, 560 025, India Tel: 91-80-2290061 Fax: 91-80-2290062

Japan

Microchip Technology Intl. Inc. Benex S-1 6F 3-18-20, Shinyokohama Kohoku-Ku, Yokohama-shi Kanagawa, 222-0033, Japan Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea

Microchip Technology Korea 168-1, Youngbo Bldg. 3 Floor Samsung-Dong, Kangnam-Ku Tel: 82-2-554-7200 Fax: 82-2-558-5934 **ASIA/PACIFIC** (continued)

Singapore

Microchip Technology Singapore Pte Ltd. 200 Middle Road #07-02 Prime Centre Singapore, 188980

Tel: 65-334-8870 Fax: 65-334-8850

Taiwan

Microchip Technology Taiwan 11F-3, No. 207 Tung Hua North Road Taipei, 105, Taiwan Tel: 886-2-2717-7175 Fax: 886-2-2545-0139

EUROPE

Australia

Microchip Technology Australia Pty Ltd Suite 22, 41 Rawson Street Epping 2121, NSW Australia Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

Denmark

Microchip Technology Denmark ApS Regus Business Centre Lautrup hoj 1-3 Ballerup DK-2750 Denmark Tel: 45 4420 9895 Fax: 45 4420 9910

France

Arizona Microchip Technology SARL Parc díActivite du Moulin de Massy 43 Rue du Saule Trapu Batiment A - Ier Etage 91300 Massy, France Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany

Arizona Microchip Technology GmbH Gustav-Heinemann Ring 125 D-81739 Munich, Germany Tel: 49-89-627-144 0 Fax: 49-89-627-144-44

Germany

Analog Product Sales Lochhamer Strasse 13 D-82152 Martinsried, Germany Tel: 49-89-895650-0 Fax: 49-89-895650-22

Italy

Arizona Microchip Technology SRL Centro Direzionale Colleoni Palazzo Taurus 1 V. Le Colleoni 1 20041 Agrate Brianza Milan, Italy

Tel: 39-039-65791-1 Fax: 39-039-6899883

United Kingdom

Arizona Microchip Technology Ltd. 505 Eskdale Road Winnersh Triangle Wokingham Berkshire, England RG41 5TU Tel: 44 118 921 5869 Fax: 44-118 921-5820

All rights reserved. © 2001 Microchip Technology Incorporated. Printed in the USA. 1/01 🚺 Printed on recycled paper.

Information contained in this publication regarding device applications and the like is intended through suggestion only and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. No representation or warranty is given and no liability is assumed by Microchip Technology Incorporated with respect to the accuracy or use of such information, or infringement of patents or other intellectual property rights arising from such use or otherwise. Use of Microchipis products as critical components in life support systems is not authorized except with express written approval by Microchip. No licenses are conveyed, implicitly or otherwise, except as maybe explicitly expressed herein, under any intellectual property rights. The Microchip logo and name are registered trademarks of Microchip Technology Inc. in the U.S.A. and other countries. All rights reserved. All other trademarks mentioned herein are the property of their respective companies.

© 2001 Microchip Technology Inc. DS21371A 10 TC1235/6/7-1 3/24/00